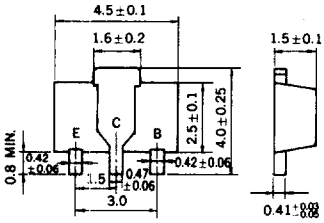
SILICON TRANSISTORS
2SB1115,2SB1115A

PNP SILICON EPITAXIAL TRANSISTOR
POWER MINI MOLD

DESCRIPTION

2SB1115, 2SB1115A are designed for audio frequency power amplifier and switching application, especially in Hybrid Integrated Circuits.

PACKAGE DIMENSIONS
in millimeters



1. Emitter
2. Collector
3. Base

FEATURES

- World Standard Miniature Package
- Low $V_{CE(sat)}$. $V_{CE(sat)}$ = −0.2 V at 1 A
- Complement to 2SD1615, 2SD1615A

ABSOLUTE MAXIMUM RATINGS

Maximum Voltages and Currents (T_a = 25 °C)

		2SB1115	2SB1115A	
Collector to Base Voltage	V_{CBO}	−60	−80	V
Collector to Emitter Voltage	V_{CEO}	−50	−60	V
Emitter to Base Voltage	V_{EBO}	−6		V
Collector Current (DC)	I_C	−1		A
Collector Current (Pulse)*	I_C	−2		A
Maximum Power Dissipation				
Total Power Dissipation at 25 °C Ambient Temperature**	P_T	2.0		W
Maximum Temperatures				
Junction Temperature	T_j	150		°C
Storage Temperature Range	T_{stg}	−55 to +150		°C

*PW ≤ 10 ms, Duty Cycle ≤ 50 %

**When mounted on ceramic substrate of 2.5 cm² x 0.7 mm

ELECTRICAL CHARACTERISTICS (T_a = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS	
Collector Cutoff Current	I_{CBO}			−100	nA	2SB1115	V_{CB} = −60 V, I_E = 0
				−100	nA	2SB1115A	V_{CB} = −80 V, I_E = 0
Emitter Cutoff Current	I_{EBO}			−100	nA	V_{EB} = −6.0 V, I_C = 0	
DC Current Gain	h_{FE1}***	135	340	600		2SB1115	V_{CE} = −2.0 V, I_C = −100 mA
		135	340	400		2SB1115A	
DC Current Gain	h_{FE2}***	100	200			V_{CE} = −2.0 V, I_C = −1.0 A	
Collector Saturation Voltage	$V_{CE(sat)}$***		−0.2	−0.3	V	I_C = −1.0 A, I_B = −50 mA	
Base Saturation Voltage	$V_{BE(sat)}$***		−0.9	−1.2	V	I_C = −1.0 A, I_B = −50 mA	
Base to Emitter Voltage	V_{BE}***	−600		−700	mV	V_{CE} = −2.0 V, I_C = −50 mA	
Gain Bandwidth Product	f_T	80	120		MHz	V_{CE} = −2.0 V, I_E = −100 mA	
Output Capacitance	C_{ob}		25		pF	V_{CB} = −10 V, I_E = 0, f = 1.0 MHz	

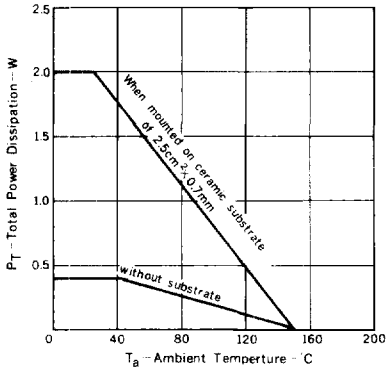
***Pulsed: PW ≤ 350 μs, Duty Cycle ≤ 2 %

h_{FE} Classification

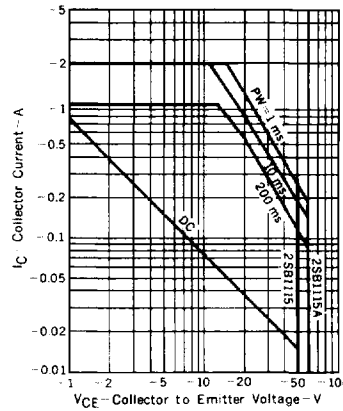
MARKING	2SB1115	YM	YL	YK
	2SB1115A	YQ	YP	
h_{FE}		135 to 270	200 to 400	300 to 600

TYPICAL CHARACTERISTICS (T_a = 25 °C)

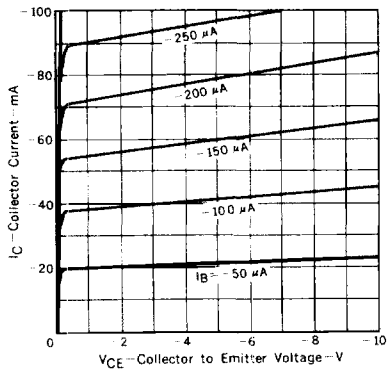
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



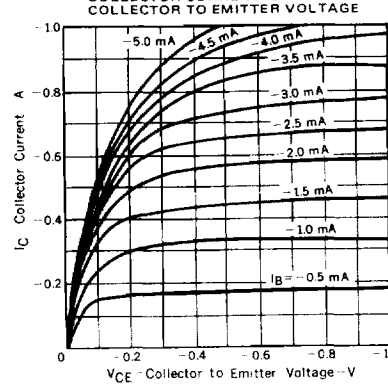
SAFE OPERATING AREA (TRANSIENT THERMAL RESISTANCE METHOD)



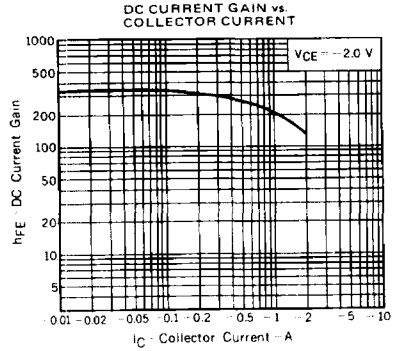
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



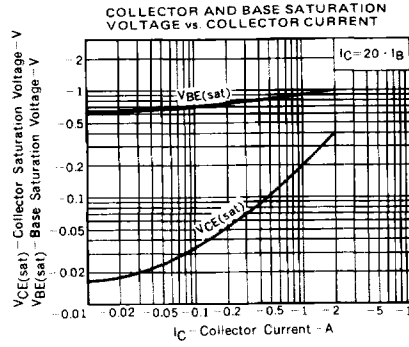
COLLECTOR CURRENT vs. COLLECTOR TO EMITTER VOLTAGE



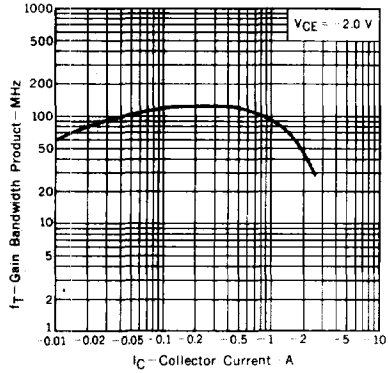
DC CURRENT GAIN vs. COLLECTOR CURRENT



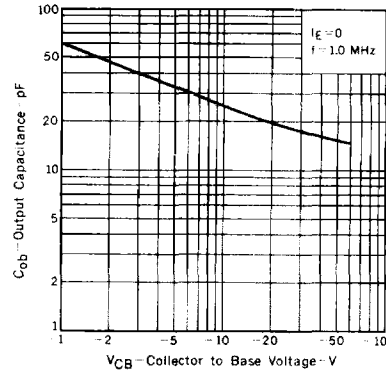
COLLECTOR AND BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



GAIN BANDWIDTH PRODUCT vs.
EMITTER CURRENT



OUTPUT CAPACITANCE vs.
COLLECTOR TO BASE VOLTAGE



SWITCHING TIME vs.
COLLECTOR CURRENT